



<b>Substitute for form 1449A/PTO</b> <b>INFORMATION DISCLOSURE</b> <b>STATEMENT BY APPLICANT</b>				<b>Complete if Known</b>	
				Application Number	10/816,282
<b>Sheet</b> <b>1</b> <b>of</b> <b>1</b>				Filing Date	March 31, 2004
				First Named Inventor	Peter L.D. Chang
				Art Unit	2818
				Examiner Name	
				Attorney Docket Number	42P18252

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.†	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
PH		FRIED, David et al., "High-Performance P-Type Independent-Gate FinFETs," IEEE Electron Device Letters, Vol. 25, No. 4, April 2004, pgs. 199-201.	
I		FRIED, David et al., "Improved Independent Gate N-Type FinFET Fabrication and Characterization," IEEE Electron Device Letters, Vol. 24, No. 9, Sept. 2003, pgs. 592-594.	
I		KUO, Charles et al., "Capacitorless Double-Gate DRAM Cell Design for High Density Applications," IEDM, 2002, pages 843-846.	
I		CHAN, Mansun et al., "Recessed-Channel Structure for Fabricating Ultrathin SOI MOSFET with Low Series Resistance," IEEE Electron Device Letters, Vol. 15, No. 1, Jan. 1994, 3	
PH		OHSAWA, Takashi et al., "Memory Design Using a One-Transistor Gain Cell on SOI," IEEE Jnl of Solid-State Circuits, Vol. 37, No. 11, Nov. 2002, pages 1510-1522.	

<b>Examiner Signature</b>	PH-TH HO	<b>Date Considered</b>	July 2005
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\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

†Applicant's unique citation designation number. †Applicant is to place a check mark here if English language Translation is attached.